

Features

- $V_{DS} = -20V, I_D = -3A$
 $R_{DS(ON)} = 120m\Omega @ V_{GS} = -2.5V$ (Typ)
 $R_{DS(ON)} = 85m\Omega @ V_{GS} = -4.5V$ (Typ)
- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

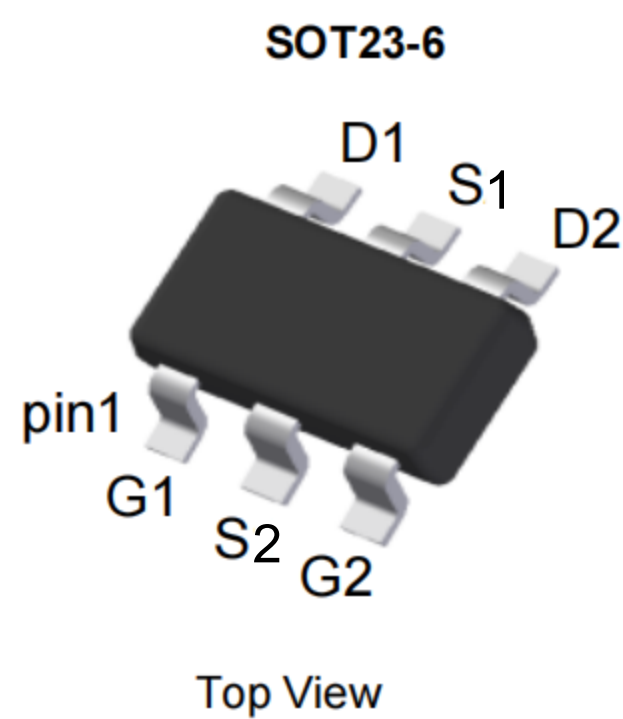
Application

- PWM applications
- Power management

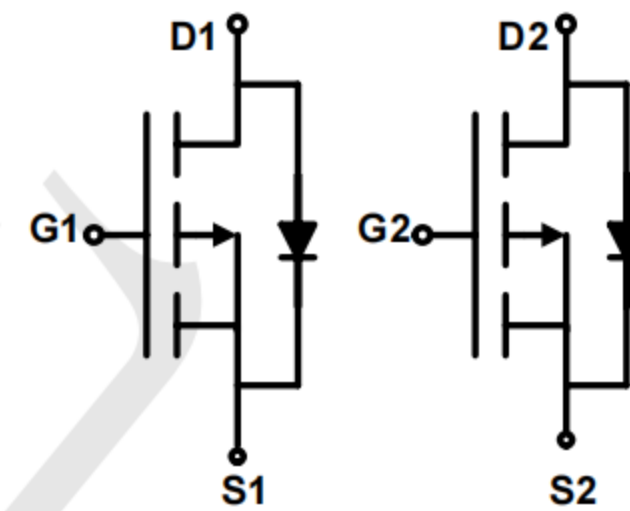
Ordering Information

- Package: SOT23-6
- Shipping Qty: 3000/7inch Tape Reel

Package and Pin Configuration



Circuit diagram



Marking: 312F

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

TECH PUBLIC Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 10	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	-3	A
	I_{DM}	-10	A
Maximum Power Dissipation	P_D	1.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	110	$^\circ C/W$
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5		-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-3A$		85	100	m Ω
		$V_{GS}=-2.5V, I_D=-2A$		120	150	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-3A$		7		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-10V, V_{GS}=0V, F=1.0MHz$		300		PF
Output Capacitance	C_{oss}			65		PF
Reverse Transfer Capacitance	C_{rss}			50		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-10V, I_D=-1A, V_{GS}=-4.5V, R_{GEN}=6\Omega$		12		nS
Turn-on Rise Time	t_r			15		nS
Turn-Off Delay Time	$t_{d(off)}$			80		nS
Turn-Off Fall Time	t_f			45		nS
Total Gate Charge	Q_g	$V_{DS}=-10V, I_D=-3A, V_{GS}=-4.5V$		6		nC
Gate-Source Charge	Q_{gs}			1		nC
Gate-Drain Charge	Q_{gd}			2.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1.25A$			-1.2	V

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

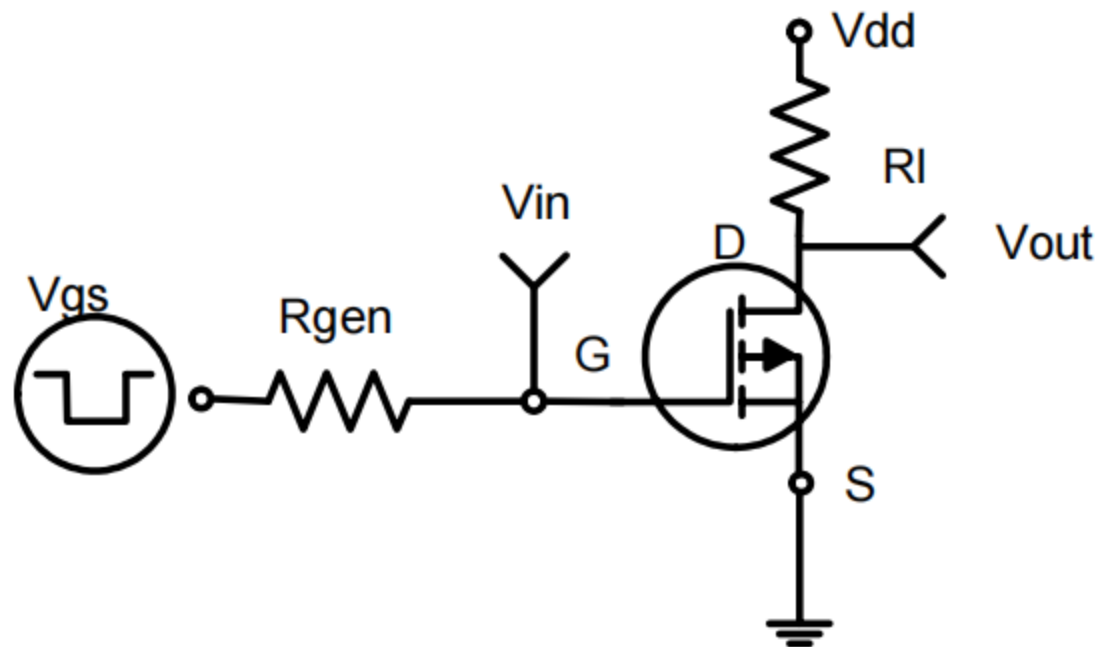


Figure1:Switching Test Circuit

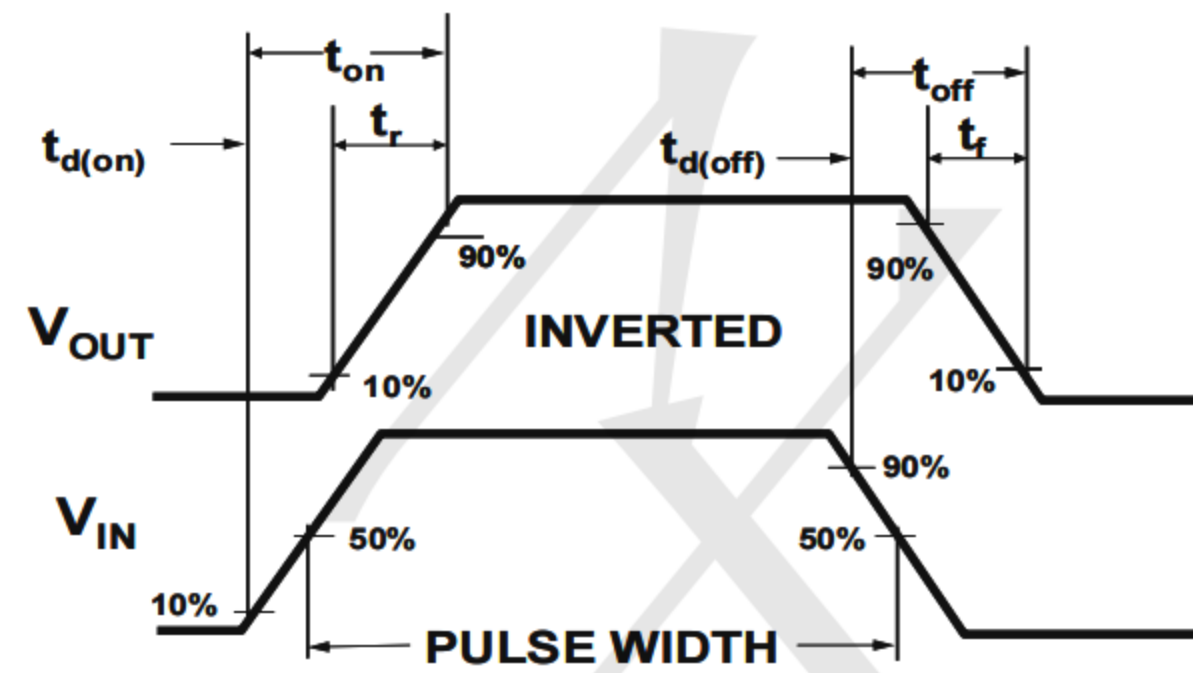


Figure 2:Switching Waveforms

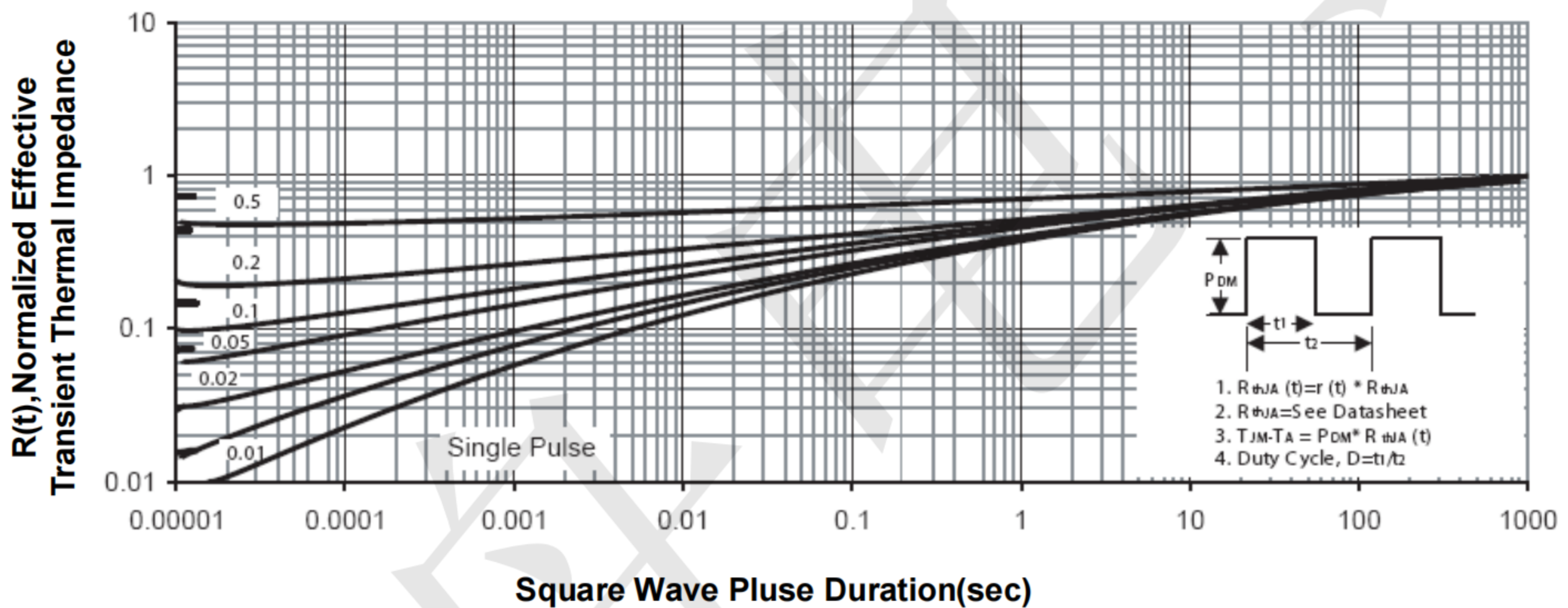


Figure 3: Normalized Maximum Transient Thermal Impedance



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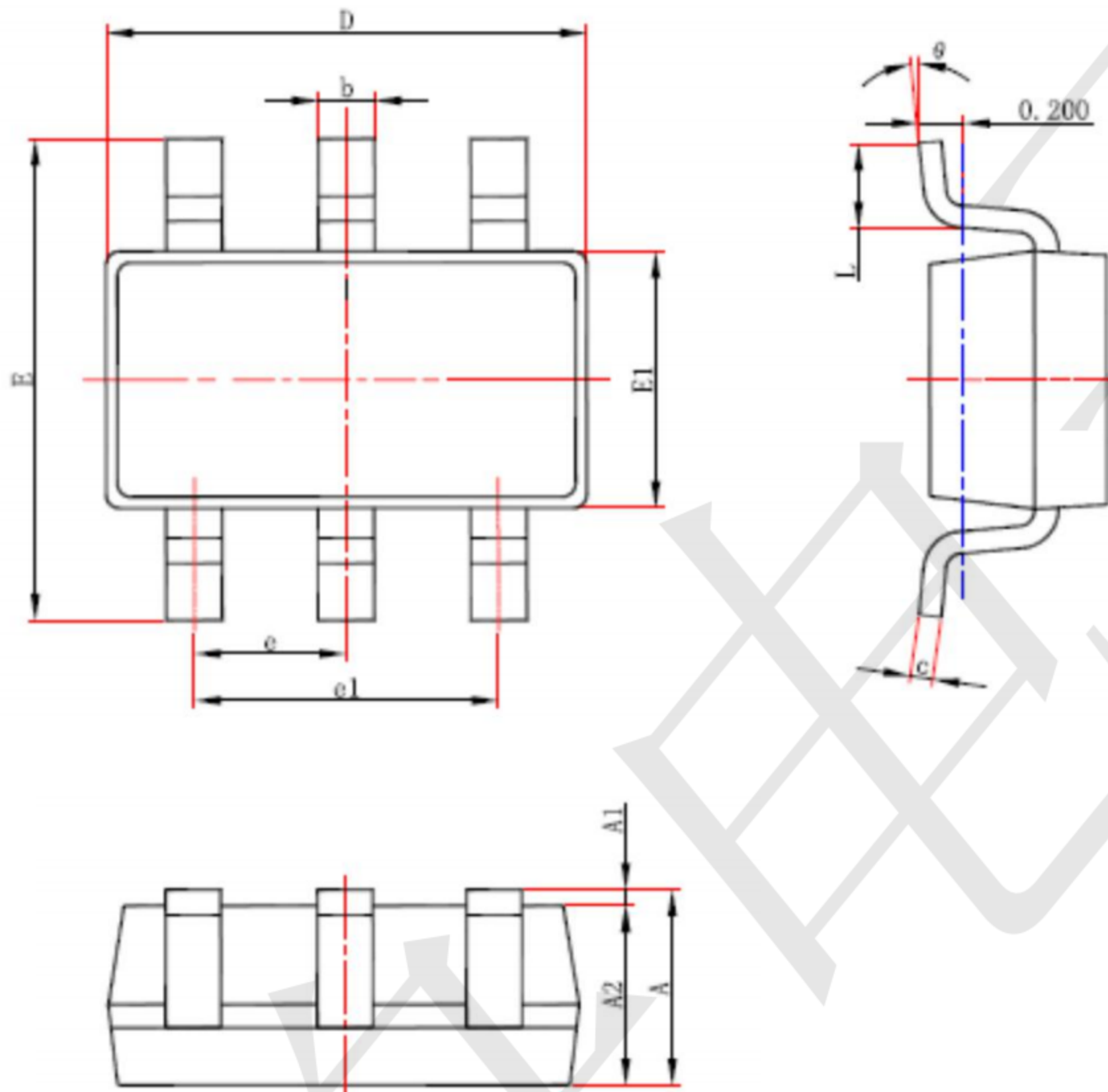
—台丹电子—

TPM20PB3S6-1

Dual P-Channel 20V (D-S) MOSFET

www.sot23.com.tw

SOT23-6 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°